

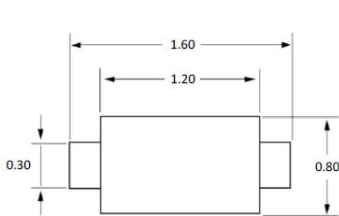
Description

The SD05CH is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The SD05CH complies with the IEC 61000-4-2 (ESD) with ± 30 kV air and ± 30 kV contact discharge. It is assembled into an ultra-small SOD-523 lead-free package. The small size and high ESD surge protection make SD05CH an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

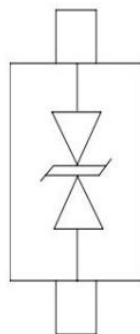
Features

- Low leakage: nA level
- Operating voltage: 5V
- Ultra low clamping voltage
- One data line protects
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ± 25 kV
 - Contact discharge: ± 20 kV
 - IEC61000-4-5 (Lightning)20A (8/20uS)
- RoHS Compliant

Dimensions & Symbol (Unit: mm Max)



Package Dimensions



Circuit and Pin Schematic

Mechanical Characteristics

- Package: SOD-523
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

Marking Information



Ordering Information

Part Number	Packaging	Reel Size
SD05CH	5000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power ($t_p=8/20\mu\text{s}$ waveform)	P_{ppp}	300	W
Peak Pulse Current (8/20 μs)	I_{pp}	20	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 25	kV
ESD per IEC 61000-4-2 (Contact)		± 20	
Operating Temperature Range	T_J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	6			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.5	μA	$V_{RWM} = 5\text{V}$
Clamping Voltage	V_C			15	V	$I_{PP} = 20\text{A}$ (8 x 20 μs pulse)
Junction Capacitance	C_J		40	50	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)

Figure 1: Peak Pulse Power Vs Pulse Time

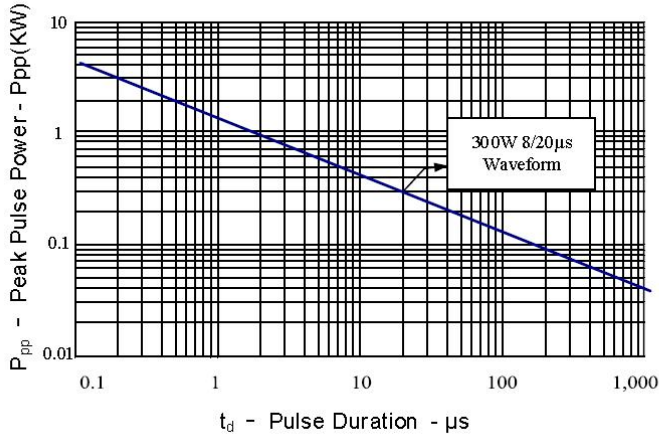


Figure 2: Power Derating Curve

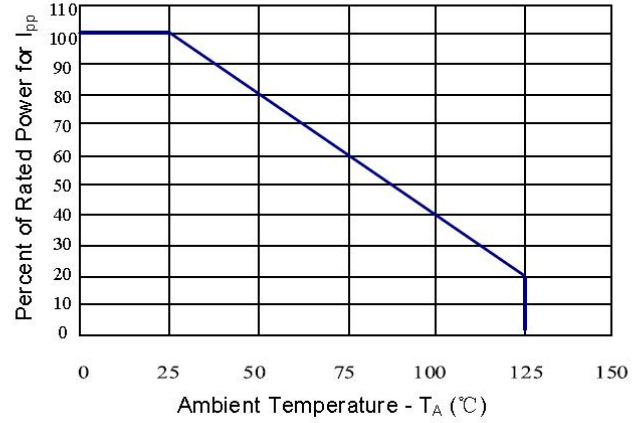


Figure 3: Clamping Voltage vs. Peak Pulse Current

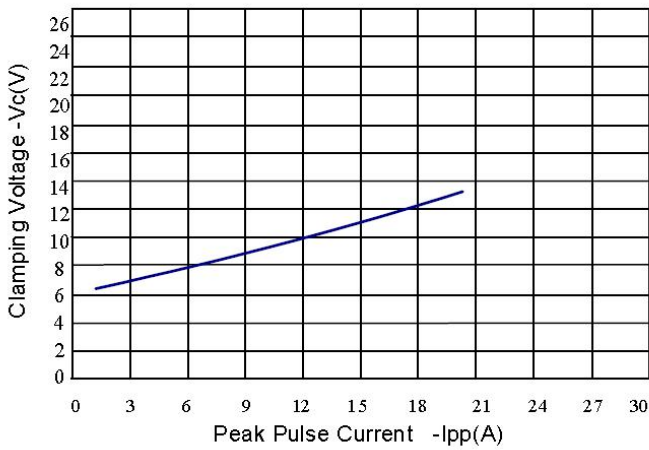


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

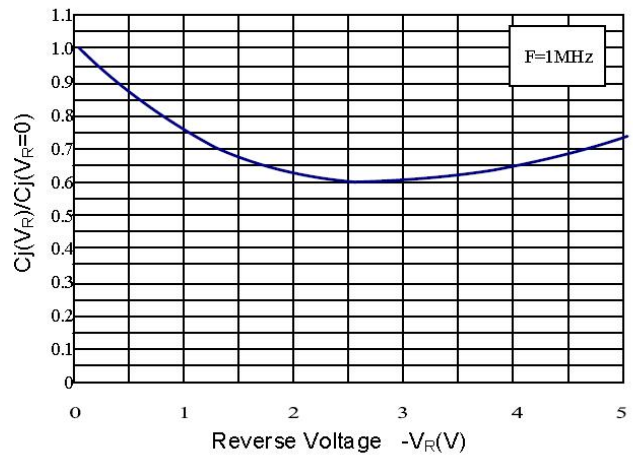


Figure 5: TLP Positive I-V Curve

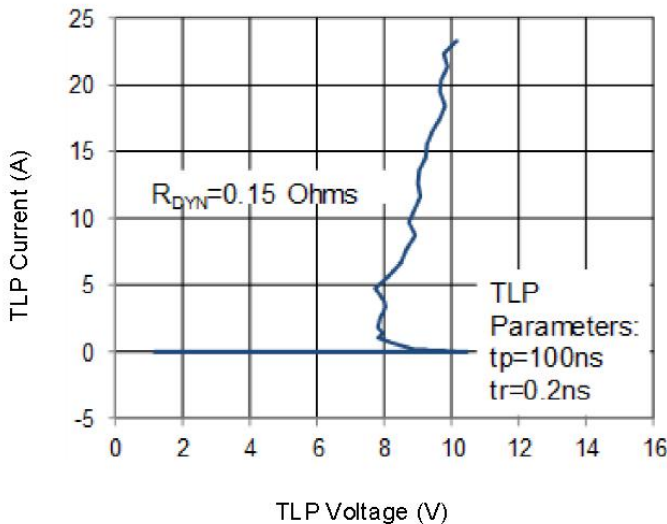
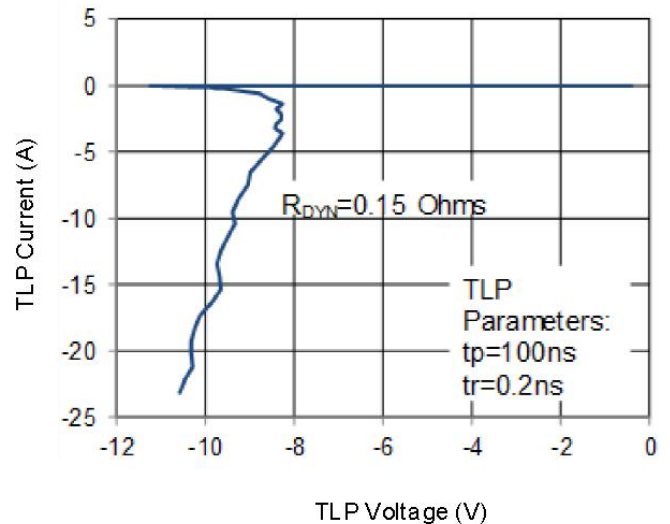
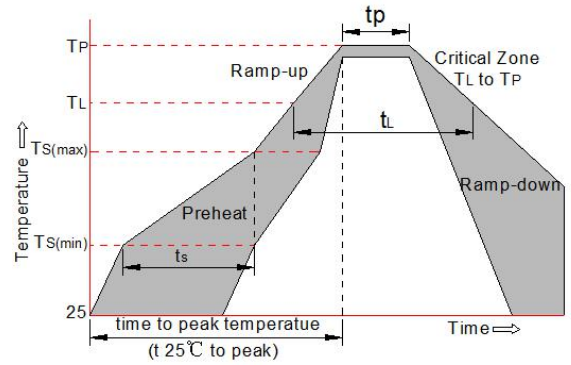


Figure 6: TLP Negative I-V Curve

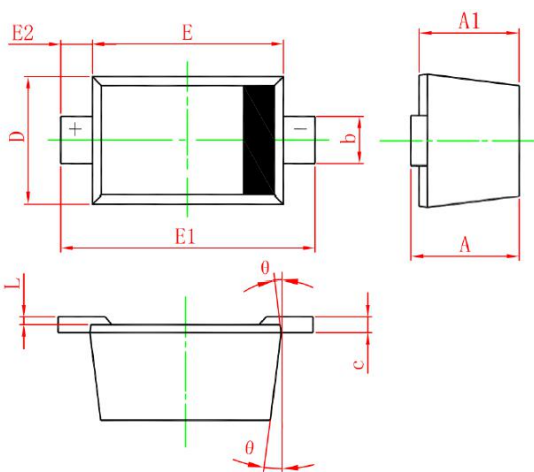


Soldering Parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

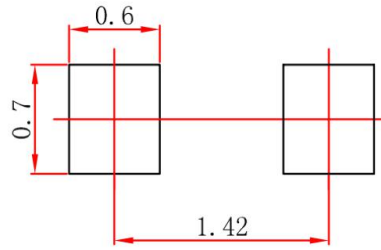


Package Mechanical Data



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.51	-	0.77	0.020	-	0.031
A1	0.50	-	0.70	0.020	-	0.028
b	0.25	-	0.35	0.010	-	0.014
c	0.08	-	0.15	0.003	-	0.006
D	0.75	-	0.85	0.030	-	0.033
E	1.10	-	1.30	0.043	-	0.051
E1	1.50	-	1.70	0.059	-	0.067
E2	0.20REF			0.008REF		
L	0.01	-	0.07	0.001	-	0.003
Φ	7° REF			7° REF		

Suggested Land Pattern



Tape size

Unit: mm

